

566.40894X00

APPENDIX A

Experimental Results

Concrete Experiments	Glass Substrate	Process Condition (Formation of SiO ₂ Film)	Characteristics	
			Glass Compaction During Process	V _{FB} *
No. 1 Present Invention	Defined Claim 1	Temp: 450° C, Time: 30 min. (See page 11, lines 13 -)	8 ~ 10 ppm	V _{FB} : 0 ~ 0.2V
No. 2	↑	Yamazaki (USP 6,025,630) Temp: 550° C, Time: 1 hr (See col. 7, lines 14 -)	About 60 ppm	Impossible to fabricate devices
No. 3	↑	Abe (JP H8-195494) Temp: 600° C, Time: 30 min.** (See col. 9, paragraph [0055])	About 90 ppm	↑
No. 4	Annealed	Yamazaki (USP 6,025,630) Temp: 550° C, Time: 1 hr (See col. 7, line 14 -)	About 6 ppm	V _{FB} : ~ 0V

* V_{FB}: Flatband Voltage

**Time is estimated using process temperature and thickness of oxide film